

Ha Sul Kim

List of Publications by Year in descending order

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8
papers

727
citations

1307594
7
h-index

1588992
8
g-index

8
all docs

8
docs citations

8
times ranked

1266
citing authors

| # | ARTICLE | IF | CITATIONS |
|---|--|------|-----------|
| 1 | Ultrathin compound semiconductor on insulator layers for high-performance nanoscale transistors. Nature, 2010, 468, 286-289. | 27.8 | 373 |
| 2 | Quantum Confinement Effects in Nanoscale-Thickness InAs Membranes. Nano Letters, 2011, 11, 5008-5012. | 9.1 | 97 |
| 3 | Nanoscale InGaSb Heterostructure Membranes on Si Substrates for High Hole Mobility Transistors. Nano Letters, 2012, 12, 2060-2066. | 9.1 | 85 |
| 4 | Ultrathin body InAs tunneling field-effect transistors on Si substrates. Applied Physics Letters, 2011, 98, . | 3.3 | 76 |
| 5 | Benchmarking the performance of ultrathin body InAs-on-insulator transistors as a function of body thickness. Applied Physics Letters, 2011, 99, . | 3.3 | 40 |
| 6 | Ultrathin-Body High-Mobility InAsSb-on-Insulator Field-Effect Transistors. IEEE Electron Device Letters, 2012, 33, 504-506. | 3.9 | 28 |
| 7 | Strain engineering of epitaxially transferred, ultrathin layers of III-V semiconductor on insulator. Applied Physics Letters, 2011, 98, 012111. | 3.3 | 23 |
| 8 | The effect of absorber doping on electrical and optical properties of nBn based type-II InAs/GaSb strained layer superlattice infrared detectors. Applied Physics Letters, 2009, 95, 121110. | 3.3 | 5 |